

*a1 added S 7*  
10. The crystalline silicon thin film semiconductor device according to claim 5, wherein the third and fourth polycrystalline silicon layers contain not less than 0.1% of hydrogen.

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*a2*  
16. The process *BA* according to claim 14, wherein the amorphous silicon layer has a thickness of not more than 50 nm.

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09025626-081001